

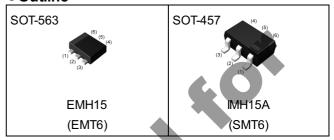
General purpose (dual digital transistor)

Parameter	DTr1 and DTr2
V <sub>CEO</sub>	50V
I <sub>C</sub>	100mA
R <sub>1</sub>	47kΩ

## Features

- 1)Two DTC144T chips in a EMT or SMT package.
- 2)Mounting possible with EMT3 or SMT3 automatic mounting machines.
- 3)Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

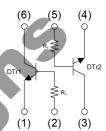
#### Outline



### •Inner circuit

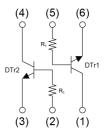
#### EMH15

- (1) DTr1 Emitte
- (2) DTr1 Base
- (3) DTr2 Collector
- (4) DTr2 Emitter
- (5) DTr2 Base
- (6) DTr1 Collector



#### IMH15A

- (1) DTr1 Collector
- (2) DTr2 Base
- (3) DTr2 Emitter
- (4) DTr2 Collector
- (5) DTr1 Base
- (6) DTr1 Emitter



# Application

INVERTER, INTERFACE, DRIVER

### Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
EMH15	SOT-563 (EMT6)	1616	T2R	180	8	8000	H15
IMH15A	SOT-457 (SMT6)	2928	T110	180	8	3000	H15

# ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

### <For DTr1 and DTr2 in common>

Parameter			Symbol	Values	Unit	
Collector-base voltage		$V_{CBO}$	50	V		
Collector-emitter voltage		V <sub>CEO</sub>	50	V		
Emitter-base voltage		V <sub>EBO</sub>	5	V		
Collector current		I <sub>C</sub>	100	mA		
Device die einetien	EMH15		P <sub>D</sub> *1*2	150	m\\//Tata	
Power dissipation	IMH15A		P <sub>D</sub> *1*3	300	mW/Total	
Junction temperature		Tj	150	°C		
Range of storage temperature		T <sub>stg</sub>	-55 to +150	°C		

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

## <For DTr1 and DTr2 in common>

● Electrical characteristics (T <sub>a</sub> <for and="" comm<="" dtr1="" dtr2="" in="" th=""><th>•</th><th></th><th></th><th>5</th><th>)</th><th></th></for>	•			5	)	
Parameter	Symbol	Conditions	Min.	Values Typ.	Max.	Unit
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> = 50μΑ	5	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 50V	-	-	500	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	-	-	500	nA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA	-	-	300	mV
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 1mA	100	250	600	-
Input resistance	R <sub>1</sub>	-	32.9	47	61.1	kΩ
Transition frequency	f <sub>T</sub> *4	V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz	-	250	-	MHz

<sup>\*1</sup> Each terminal mounted on a reference land.

<sup>\*2 120</sup>mW per element must not be exceeded.

<sup>\*3 200</sup>mW per element must not be exceeded.

<sup>\*4</sup> Characteristics of built-in transistor.

# ● Electrical characteristic curves (T<sub>a</sub> = 25°C)

<For DTr1 and DTr2 in common>

Fig.1 Grounded Emitter Propagation Characteristics

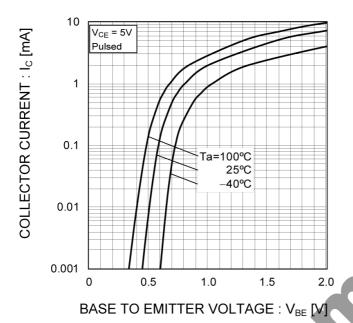


Fig.2 Grounded Emitter Output Characteristics

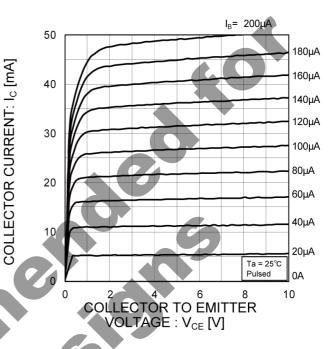


Fig.3 DC Current Gain vs. Collector Current

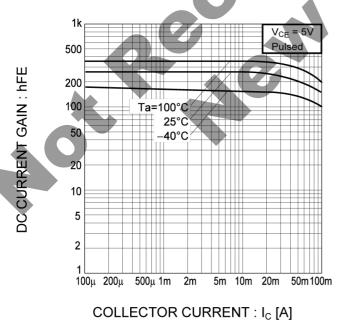
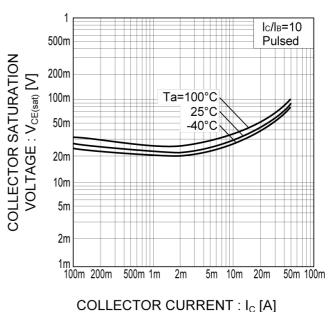
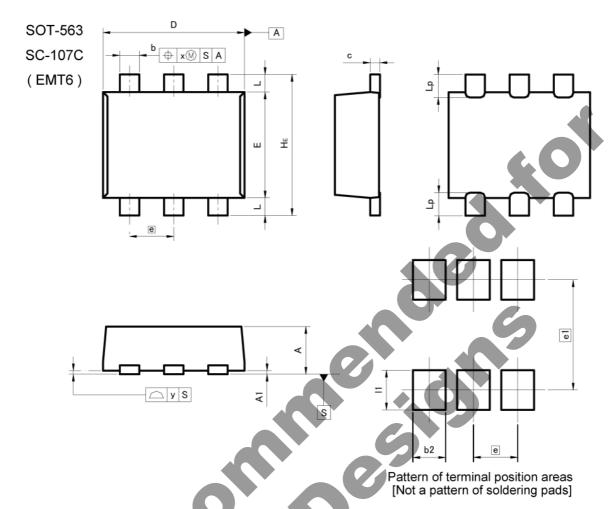


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current



# Dimensions



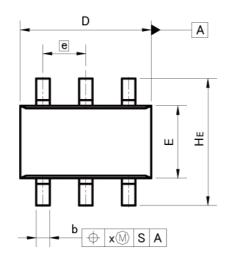
DIM		ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
A	0.45	0.55	0.018	0.022	
A1	0.00	0.10	0.000	0.004	
b	0.17	0.27	0.007	0.011	
C	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
E	1.10	1.30	0.043	0.051	
е	0.50		0.020		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	_	0.35	1	0.014	
x	_	0.10		0.004	
У	_	0.10	-	0.004	

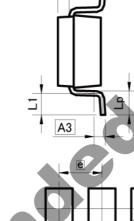
DIM	MILIMETERS		INCHES			
DIM MIN MAX		MAX	MIN	MAX		
b2	_	0.37	-	0.015		
e1	1.2	25	0.0	49		
- 11	-	0.45	-	0.018		

Dimension in mm/inches

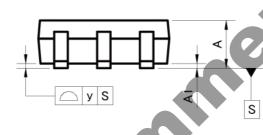
# Dimensions

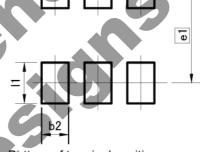






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Pattern of terminal position areas [Not a pattern of soldering pads]

DIM	MILIMETERS		INCHES		
DIW	MIN	MAX	MIN	MAX	
A	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0.000	0.004	
A3	0.:	25	0.0	10	
b	0.25	0.40	0.010	0.016	
С	0.09	0.25	0.004	0.010	
D	2.80	3.00	0.110	0.118	
E	1.50	1.80	0.059	0.071	
е	0.9	95	0.037		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	-	0.20	-	0.008	
У	-	0.10	-	0.004	

DIM	MILIMETERS		INCHES	
DIM MIN		MAX	MIN	MAX
b2		0.60	-	0.024
e1	2.	10	0.083	
11		0.90	<del>-</del>	0.035

Dimension in mm/inches

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